

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3007090	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/17 16:19
L2	1	1 and capacitor with (nrom or nitride adj read adj only) adj3 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/17 16:38
L3	8	1 and capacitor with (nrom or nitride adj read adj only)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/17 16:29
L4	2	("6440798").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/01/17 16:29
L5	44	1 and capacitor with (nrom or nitride) adj5 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/17 16:32
L6	22	5 and (word or wordline)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/17 16:32
L7	357	1 and capacitor with (nonvolatile or non-volatile or floating adj gate) adj3 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/17 16:39
L9	86	7 and (dynamic or dram) and (read adj only or \$3rom)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/17 16:41
L10	40	9 and (nitride or nrom)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/01/17 16:42